

Small Signal Diode



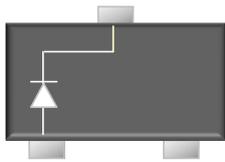
Features

- ◇Fast switching speed
- ◇Surface device type mounting
- ◇Moisture sensitivity level 1
- ◇Matte Tin(Sn) lead finish with Nickel(Ni) underplate
- ◇Pb free version and RoHS compliant
- ◇Green compound (Halogen free) with suffix "G" on packing code and prefix "G" on date code

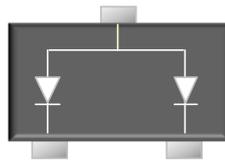
Mechanical Data

- ◇Case :SOT-23 small outline plastic package
- ◇Terminal: Matte tin plated, lead free., solderable per MIL-STD-202, Method 208 guaranteed
- ◇High temperature soldering guaranteed: 260°C/10s
- ◇Weight : 0.008gram (approximately)
- ◇Marking Code : JS,JS2,JS3,JS4

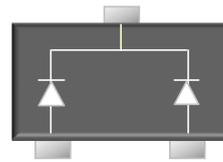
Pin Configuration



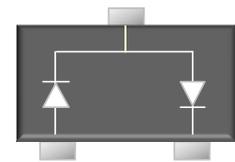
BAS21



BAS21A



BAS21C



BAS21S

Ordering Information

Package	Part No.	Packing	Marking
SOT-23	BAS21 RF	3K / 7" Reel	JS
SOT-23	BAS21A RF	3K / 7" Reel	JS2
SOT-23	BAS21C RF	3K / 7" Reel	JS3
SOT-23	BAS21S RF	3K / 7" Reel	JS4
SOT-23	BAS21 RFG	3K / 7" Reel	JS
SOT-23	BAS21A RFG	3K / 7" Reel	JS2
SOT-23	BAS21C RFG	3K / 7" Reel	JS3
SOT-23	BAS21S RFG	3K / 7" Reel	JS4

Maximum Ratings and Electrical Characteristics

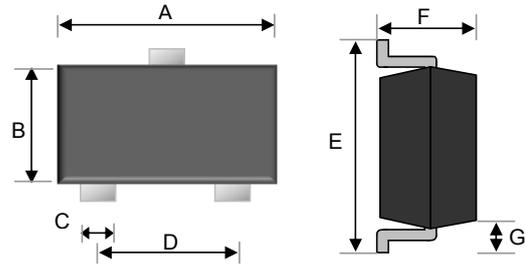
Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	P _D	225	mW
Repetitive Peak Reverse Voltage	V _{RRM}	250	V
Repetitive Peak Forward Current	I _{FRM}	625	mA
Mean Forward Current	I _O	200	mA
Non-Repetitive Peak Forward Surge Current (Note 1)	I _{FSM}	1	A
Thermal Resistance (Junction to Ambient) (Note 2)	R _{θJA}	500	°C/W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to + 150	°C

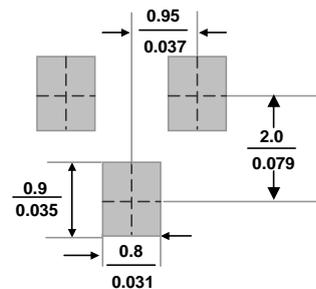
Notes:1. Test Condition : 8.3ms Single half Sine-Wave Superimposed on Rated Load (JEDEC Method) Pulse Width=1 μsec
 Notes:2. Valid provided that electrodes are kept at ambient temperature

SOT-23



Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	2.80	3.00	0.110	0.118
B	1.20	1.40	0.047	0.055
C	0.30	0.50	0.012	0.020
D	1.80	2.00	0.071	0.079
E	2.25	2.55	0.089	0.100
F	0.90	1.20	0.035	0.043
G	0.550 REF		0.022 REF	

Suggested PAD Layout



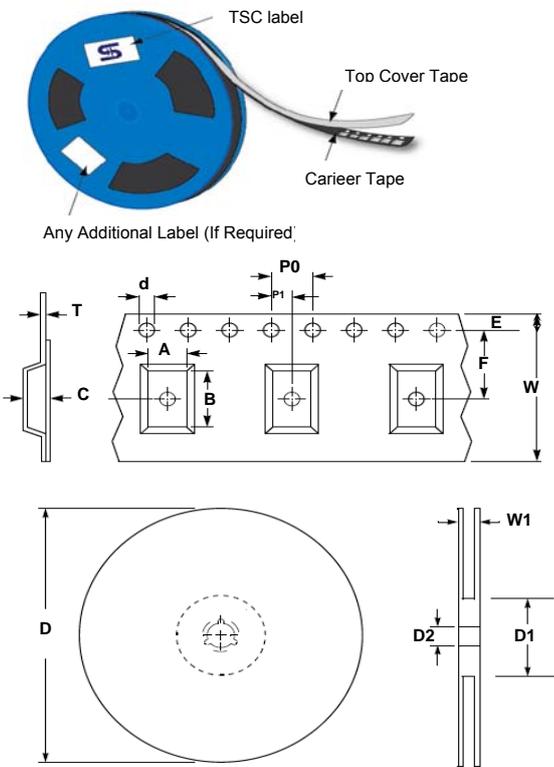
Small Signal Diode

Electrical Characteristics

Electrical Characteristics

Type Number		Symbol	Min	Max	Units
Reverse Breakdown Voltage	$I_R = 100\mu A$	$V_{(BR)}$	250	-	V
Forward Voltage	$I_F = 100mA$	V_F	-	1.00	V
	$I_F = 200mA$		-	1.25	V
Reverse Leakage Current	$V_R = 200V$	I_R	-	0.1	μA
Junction Capacitance	$V_R = 1V, f = 1.0MHz$	C_J	-	5	pF
Reverse Recovery Time	$I_F = I_R = 10mA, R_L = 100\Omega, I_{RR} = 1mA$	T_{rr}	-	50.0	ns

Tape & Reel specification



Item	Symbol	Dimension(mm)
Carrier width	A	3.15 ±0.10
Carrier length	B	2.77 ±0.10
Carrier depth	C	1.22 ±0.10
Sprocket hole	d	1.50 ± 0.10
Reel outside diameter	D	178 ± 1
Reel inner diameter	D1	55 Min
Feed hole width	D2	13.0 ± 0.20
Sprocket hole position	E	1.75 ±0.10
Punch hole position	F	3.50 ±0.05
Sprocket hole pitch	P0	4.00 ±0.10
Embossment center	P1	2.00 ±0.05
Overall tape thickness	T	0.229 ±0.013
Tape width	W	8.10 ±0.20
Reel width	W1	12.30 ±0.20

Small Signal Diode

Rating and Sharacteristic Curves

FIG 1 Typical Forward Characteristics

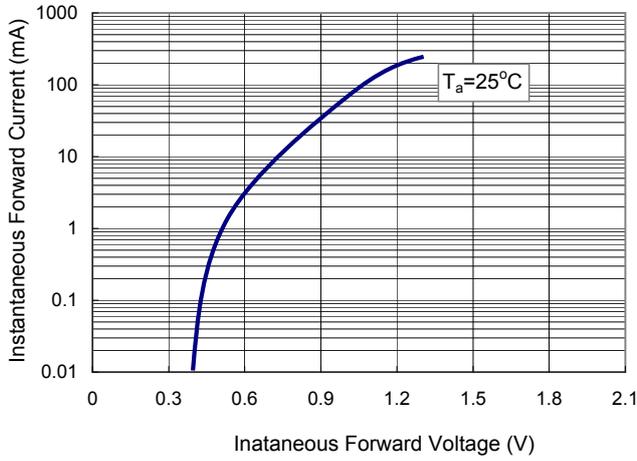


FIG 2 Reverse Current vs Junction Temperature

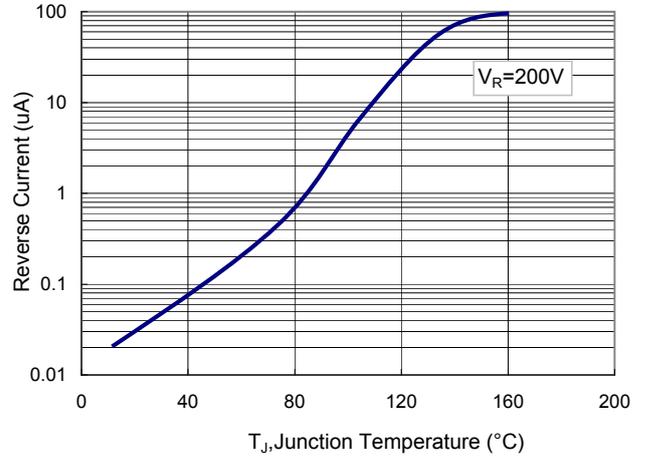
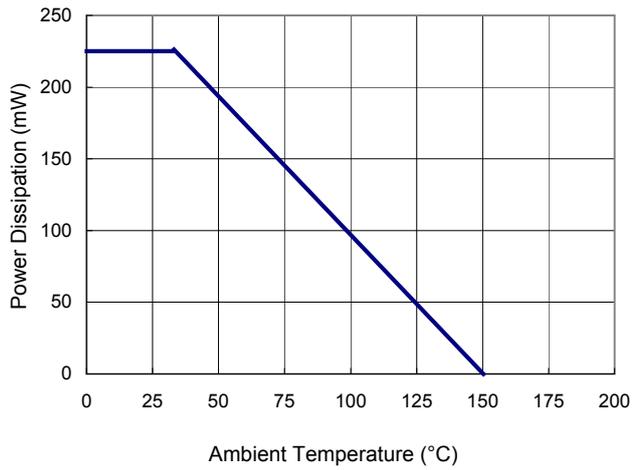


FIG 3 Admissible Power Dissipation Curve



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Taiwan Semiconductor:](#)

[BAS21](#) [BAS21A](#) [BAS21C](#) [BAS21S](#)